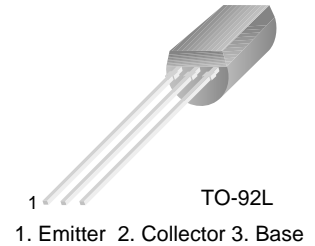


**■■ APPLICATION:** High Voltage Amplifier Applications.

**■■ MAXIMUM RATINGS** ( $T_a=25^{\circ}\text{C}$ )

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	$V_{CBO}$	300	V
Collector-emitter voltage	$V_{CEO}$	300	V
Emitter-base voltage	$V_{EBO}$	7	V
Collector current	$I_C$	100	mA
Collector Power Dissipation	$P_C$	900	mW
Junction Temperature	$T_J$	150	$^{\circ}\text{C}$
Storage Temperature Range	$T_{stg}$	- 55~150	$^{\circ}\text{C}$


**■■ ELECTRICAL CHARACTERISTICS** ( $T_a=25^{\circ}\text{C}$ )

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	$h_{FE}$	30		150		$V_{CE}=10\text{V}$ , $I_C=20\text{mA}$
Collector Cut-off Current	$I_{CBO}$			1	$\mu\text{A}$	$V_{CB}=240\text{V}$ , $I_E=0$
Emitter Cut-off Current	$I_{EBO}$			1	$\mu\text{A}$	$V_{EB}=7\text{V}$ , $I_C=0$
Collector-Base Breakdown Voltage	$BV_{CBO}$	300			V	$I_C=0.02\text{mA}$ , $I_E=0$
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	300			V	$I_C=1\text{mA}$ , $I_B=0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	7			V	$I_E=0.02\text{mA}$ , $I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			1	V	$I_C=10\text{mA}$ , $I_B=1\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1	V	$I_C=10\text{mA}$ , $I_B=1\text{mA}$
Gain bandwidth product	$f_T$	50			MHz	$I_C=20\text{mA}$ , $V_{CE}=10\text{V}$
Common Base Output Capacitance	$C_{ob}$		3		PF	$V_{CB}=20\text{V}$ , $I_E=0$ , $f=1\text{MHz}$

**■■ hFE Classification**

Classification

 $h_{FE}$ 

30~150